

**AMENDMENTS TO THE CLAIMS:**

Please amend the claims as follows:

Claims 1-6 (canceled)

7. (previously presented) A light emitting diode comprising a pellet, a major front surface of which is made of a GaAsP mixed crystal, characterized in that the major front surface is a rough surface.

8. (previously presented) A light emitting diode according to claim 7, characterized in that side surfaces of the pellet are rough surfaces.

9. (previously presented) A light emitting diode according to claim 7, characterized in that the rough surface is formed with fine projections having a diameter in a range of from 0.3  $\mu\text{m}$  to 3 $\mu\text{m}$ .

10. (previously presented) A light emitting diode according to claim 8, characterized in that the rough surface is formed with fine projections having a diameter in a range of from 0.3  $\mu\text{m}$  to 3 $\mu\text{m}$ .

11. (previously presented) A fabrication process for a light emitting diode having a pellet, a major front surface of which is made of a GaAsP mixed crystal, characterized in that the pellet is treated with an etching solution of an aqueous solution

containing Br<sub>2</sub> or I<sub>2</sub> to form fine projections on at least the major front surface of the pellet.

12. (previously presented) A fabrication process for a light emitting diode according to claim 11, characterized in that the etching solution is an aqueous solution further containing nitric acid, hydrofluoric acid and acetic acid.

13. (previously presented) A fabrication process for a light emitting diode according to claim 12, characterized in that the etching solution contains 40 to 80 parts of nitric acid, 40 to 300 parts of hydrofluoric acid and 400 to 2000 parts of acetic acid based on 1 part of Br<sub>2</sub> or I<sub>2</sub> in a molar ratio.

14. (New) The method of claim 11, wherein the fine projections have a diameter in a range of from 0.3 μm to 3μm.